

IN THE CLAIMS

1 (Currently Amended). A method comprising:
forming a source drain extension by implanting boron, ~~carbon~~, and fluorine; and
implanting fluorine to a depth deeper than boron.

2 (Original). The method of claim 1 including implanting carbon to a depth deeper than the boron implant.

Claim 3 (Canceled).

4 (Original). The method of claim 1 including implanting carbon at an energy of about 6 KeV.

5 (Original). The method of claim 4 including implanting carbon at a dose of about $1E15$ atoms/cm².

6 (Original). The method of claim 1 including performing a Halo implant before the implanting boron.

Claims 7-13 (Canceled).

14 (Withdrawn). An integrated circuit comprising:
a P-type transistor having a source drain extension including carbon and boron.

15 (Withdrawn). The circuit of claim 14 wherein said extension includes fluorine.

16 (Withdrawn). The circuit of claim 14 wherein carbon is deeper than said boron.

17 (Withdrawn). The circuit of claim 14 wherein fluorine is deeper than said boron.

Claims 18-21 (Canceled).